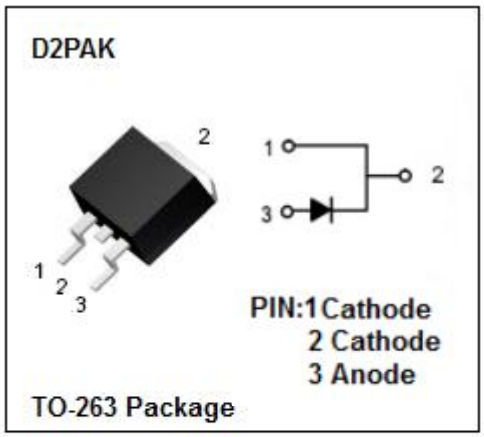
Schottky Barrier Rectifier — MBRB1060

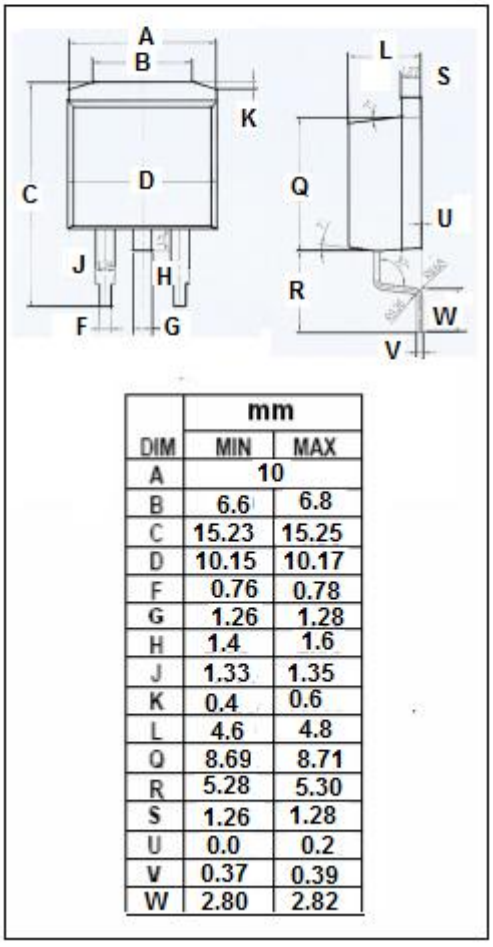
FEATURES

- Schottky Barrier Chip
- Low Power Loss/High Efficiency
- High Surge Capability
- High Current Capability，Low Forward Voltage Drop
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for low-voltage,high frequency inverters，free wheeling and polarrity protection applications.



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM}	Peak Repetitive Reverse Voltage	60	V
$I_{F(AV)}$	Average Rectified Forward Current	10	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	150	A
T_J	Junction Temperature	-65~150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2	℃/W

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ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 10A ; T_J= 25℃ I_F= 10A ; T_J= 125℃ I_F= 20A ; T_J= 25℃ I_F= 20A ; T_J= 125℃	0.80 0.70 0.95 0.85	V
I_R	Maximum Instantaneous Reverse Current	V_R=V_{RRM}, T_J= 25℃ V_R=V_{RRM}, T_J= 125℃	0.10 15	mA